	Туре	#	Hits	Search Text	DBs
<b>⊢</b>	BRS	1.1	120	recharge near period	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
8	BRS	1.2	13371	gate near pulse	us-
m	BRS	Г3	248744	low near temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
4	BRS	L4	0	1 and 2 and 3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
2	BRS	1.5	4	1 and 2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
9	BRS	91	1167	345/204.ccls.	US- PO; B
7	BRS	17	1532	345/211-213.ccls.	US- PO; B
8	BRS	Г.8	4417	345/87-92.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
Q	BRS	61	6814	6 or 7 or 8	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
10	BRS	L10	178	increase and (recharging adj time)	US- PO; B
11	BRS	L11	0	9 and 10	I; US- JPO; IDB
12	BRS	L12	2557	transistor and (temperature near characteristic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB

<b>\</b>	
1	

	Type	T #	Hits	Search Text	DBs
13	BRS	L13	22561	recharging	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
14	BRS	L14	36	12 and 13	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
15	BRS	L15	109665	rcp	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
16	BRS	L16	10	1 and 15	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
17	BRS	L17	9833	TFT and LCD	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
18	BRS	L18	401	time	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
19	BRS	L19	·	17 and 18	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Туре	#	Hits	Search Text	DBs
П	BRS	L1	120	recharge near period	us- 0;
7	BRS	1.2	13371	gate near pulse	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
3	BRS	ГЗ	248744	low near temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
4	BRS	1.4	0	1 and 2 and 3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
5	BRS	L5	4	1 and 2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
9	BRS	91	1167	345/204.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
7	BRS	17	1532	345/211-213.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
8	BRS	18	4417	345/87-92.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
6	BRS	1.9	6814	6 or 7 or 8	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
10	BRS	L10	178	increase and (recharging adj time)	us- 0;
11	BRS	L11	0	9 and 10	US- 20; 3
12	BRS	L12	2557	transistor and (temperature near characteristic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

١					
	Type	# H	Hits	Search Text	DBs
13	BRS	L13	22561	recharging	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
14	BRS	L14	36	12 and 13	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
15	BRS	L15	109665	LCD	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
16	BRS	L16	10	1 and 15	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
17	BRS	L17	9833	TFT and LCD	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
18	BRS	L:18	401	recharging adj time	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
19	BRS	L19	1	17 and 18	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
20	BRS	L20	448	circuit near recharge	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
21	BRS	L21	3	3 and 20	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Type	#	Hits	Search Text	DBs
-	BRS	L1	120	recharge near period	US-
2	BRS	1.2	13371	gate near pulse	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
т	BRS	Г.3	248744	low near temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB
4	BRS	L4	0	1 and 2 and 3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
5	BRS	Г.5	4	1 and 2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
6	BRS	Г6	1167	345/204.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
7	BRS	1.7	1532	345/211-213.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
8	BRS	Г8	4417	345/87-92.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
9	BRS	L9	6814	6 or 7 or 8	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
10	BRS	Б10	178	increase and (recharging adj	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
11	BRS	L11	0	9 and 10	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB